

SENSORS and TRANSDUCERS



Klas Hjort, Materialvetenskap

† Micromechanics

- Micromechanics - simple mechanics
- Principles of detection: piezoresistive
piezoelectric
capacitive
- Micromechanical properties
- Micromechanical sensors

MICROMECHANICS



† Micromechanics is simple mechanics:

- Mechanics like of the middle ages, but miniaturized:
- Cantilever beams, bridges, plates, and diaphragms
- Only designs of low relative tolerances!
- We detect changes in stress, position, or frequency.

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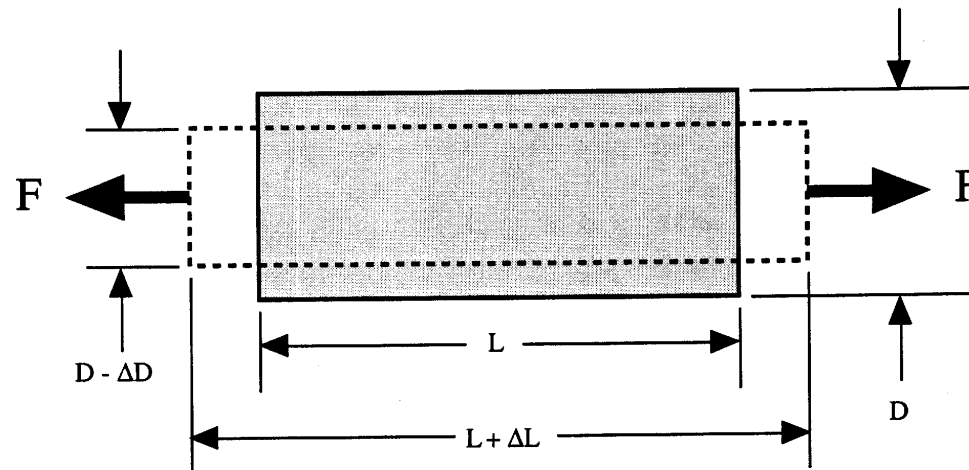
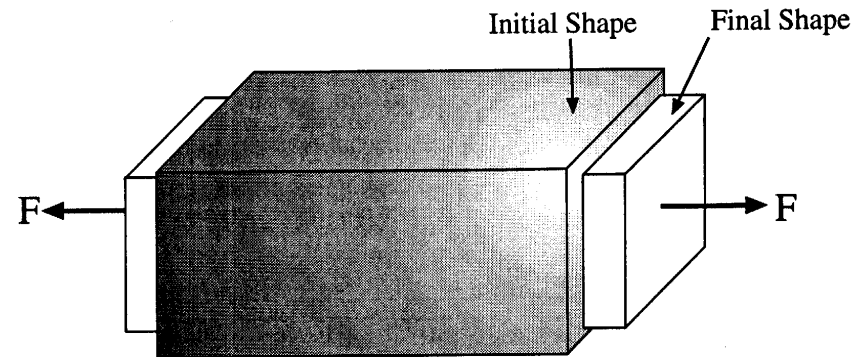
† Basic mechanics:

$$s = \frac{F}{A}$$

$$e = \frac{\Delta L}{L}$$

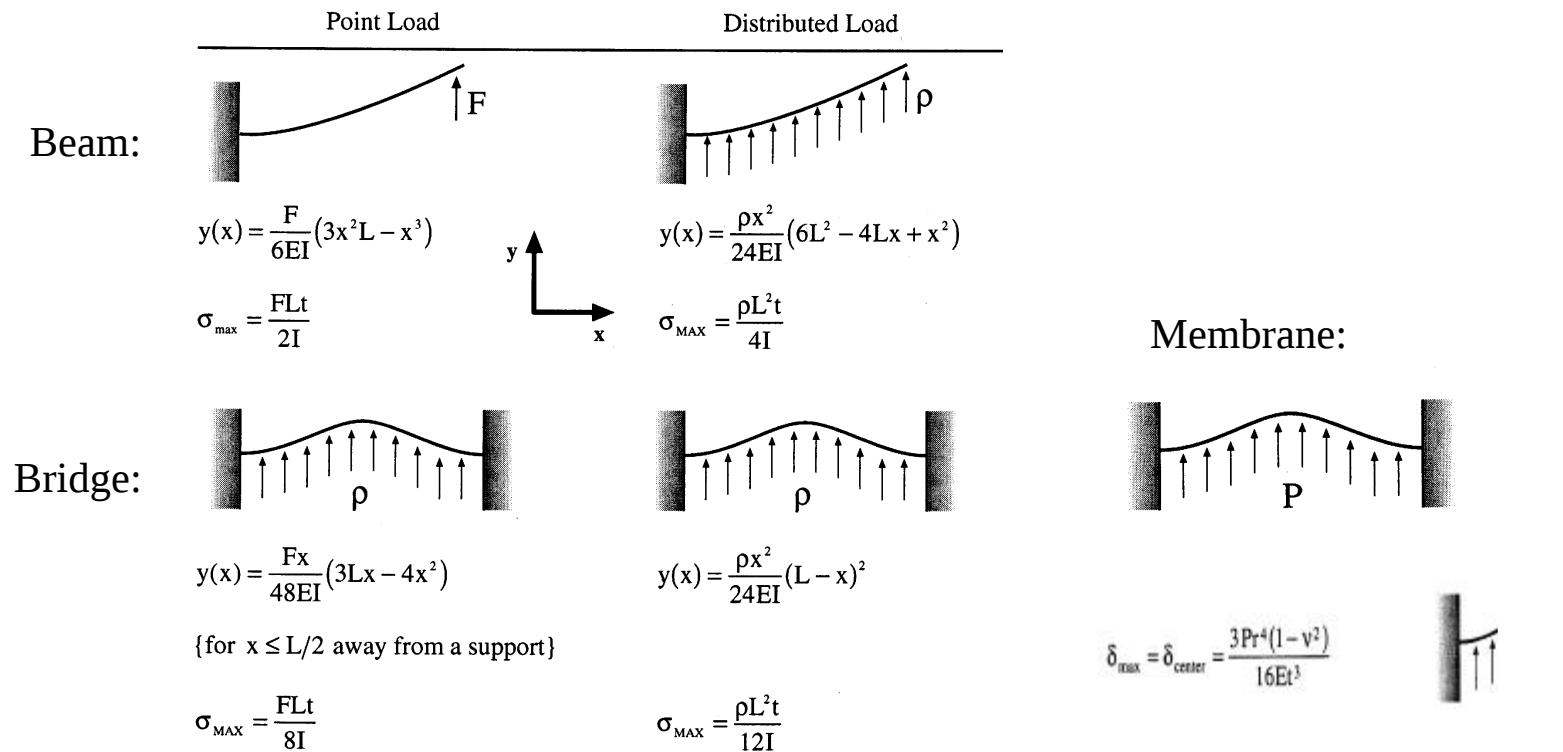
$$s = Ee$$

$$n = \frac{\frac{\Delta D}{D}}{\frac{\Delta L}{L}}$$



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† Simple mechanics:



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† Simple dynamics:

$$m \frac{d^2x}{dt^2} + b \frac{dx}{dt} + kx = F_{\text{external}}$$

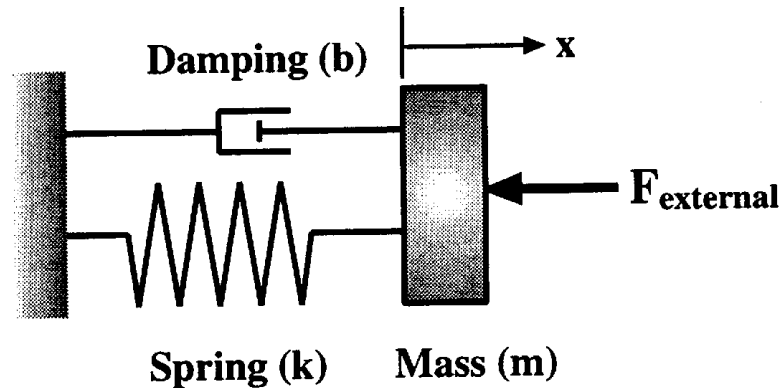
where,

m = mass, in kg

b = damping coefficient, in (N•s)/m

k = spring constant, in N/m

F_{external} = applied force, in N = (kg•m)/s²



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† Scaling mechanics:

Table 7.6 Geometric scaling factors of a cantilever beam (constant stress).

Parameter	Symbol	Factor
Beam force	F	K^2
Spring constant	k_m	K
Deflection	y	K
Beam stress	σ_m	1
Mass	m	K^3
Natural frequency	ω_o	K^{-1}

Damping: viscous (K^2), surface adhesion (K^2)

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† Mechanical properties of silicon

- Brittle
- Anisotropic
- Low ageing

<i>Property</i>	<i>Value</i>
Yield Strength	7 GPa
Hardness	10 GPa
Young's modulus	166 GPa
Density	2.33 g/m ³
Thermal conductivity	1.57 W/mK
Thermal expansion	2.6 ppm/K

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† Sensor mechanisms

Mechanism	Parameter Sensed	Needs Local Circuits?	DC Response?	Complex System?	Linearity	Issues
Metal Strain Sensor	strain	NO	YES	+	+++	• low sensitivity • very simple
Piezoresistive Strain Sensor	strain	NO	YES	+	+++	• temperature effects can be significant • easy to integrate
Piezoelectric	force	NO	NO	++	++	• high sensitivity • fabrication can be complex
Capacitive	displacement	YES	YES	++	poor	• very simple • extremely low temperature coefficients
Tunneling	displacement	YES	YES	+++	poor	• sensitive to surface states • drift performance not yet proven
Optical	displacement	NO	YES	+++	+++	• rarely employed in mechanical microsensors

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† Scaling sensor mechanisms:

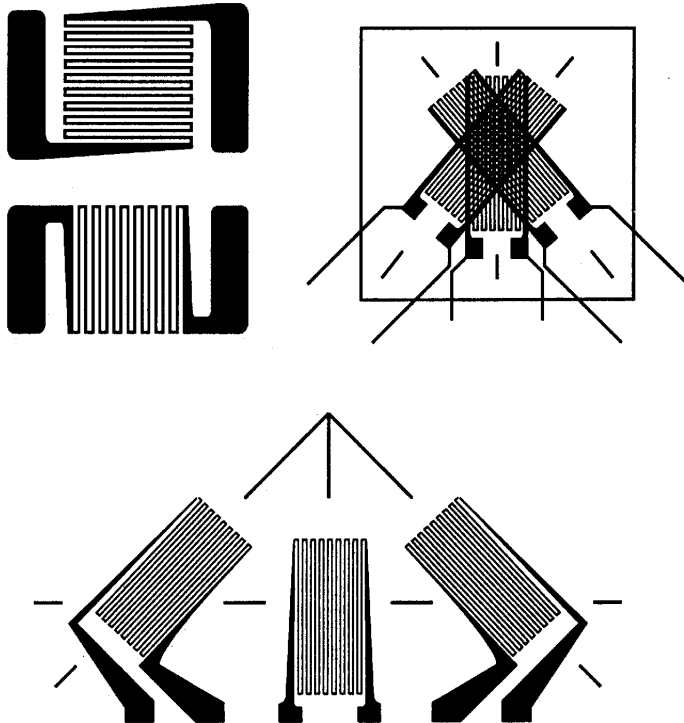
Table 7.7 Dimensions of physical sensing parameters.

Physical parameter	Electromagnetics	Electrostatics
Capacitance	$L^{-1} T^2 \mu^{B-1}$	$L \epsilon$
Inductance	$L \mu$	$L^{-1} T^2 \epsilon$
Resistance	$L T^{-1} \mu^B$	$L^{-1} T^{-1}$
Electric current	$M^{1/2} L^{1/2} T^{-1} \mu^{B-1/2}$	$M^{1/2} L^{3/2} T^{-2} \epsilon^{1/2}$
Potential difference	$M^{1/2} L^{3/2} T^{-2} \mu^{B-1/2}$	$M^{1/2} L^{1/2} T^{-1} \epsilon^{1/2}$

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† Strain gauges



Gauge factor: $GF = \frac{\Delta R}{eR}$

$$GF_{met} = (1 + 2\nu) + \frac{dr}{r} \approx 2$$

$$GF_{SC} = 80 - 200$$

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† Semiconductor bandgap

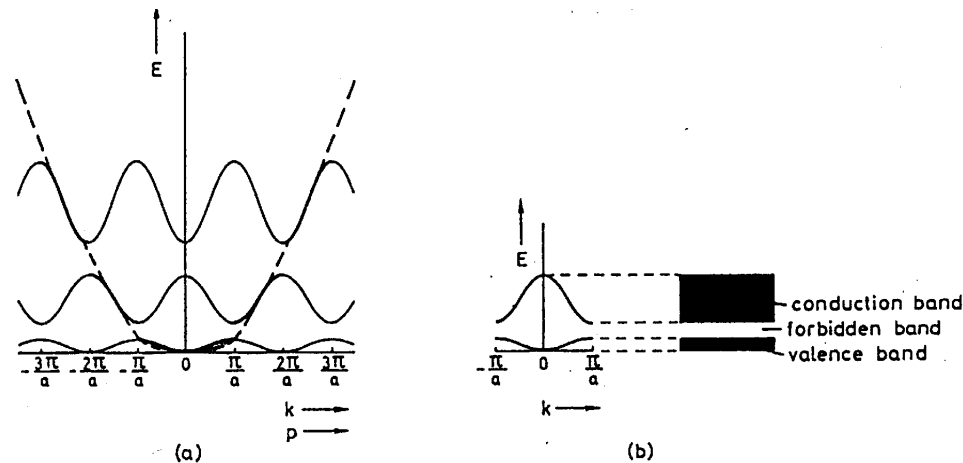


Fig. 3.2 (a) Energy E as a function of the momentum p for a classical particle (dashed line) and as a function of the wave number k for a particle with wavelike nature in interaction with a periodic crystal lattice (solid thick and thin lines), (b) part of the possible solutions indicating the conduction, the forbidden and the valence band.

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† Semiconductor bandgap in space

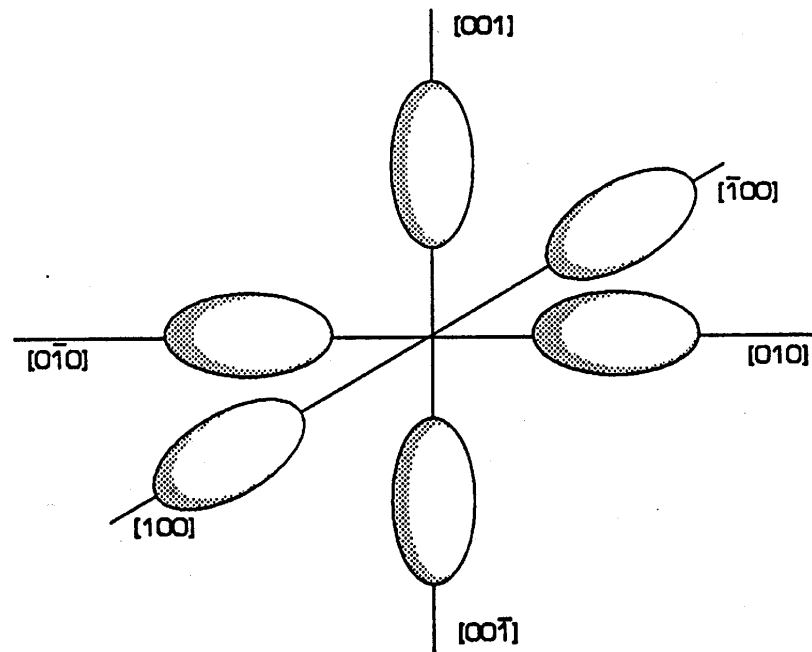


Fig. 3.4 Constant energy ellipsoids in k -space near the energy minimum in the conduction band of silicon.

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† Piezoresistive mechanism for silicon:

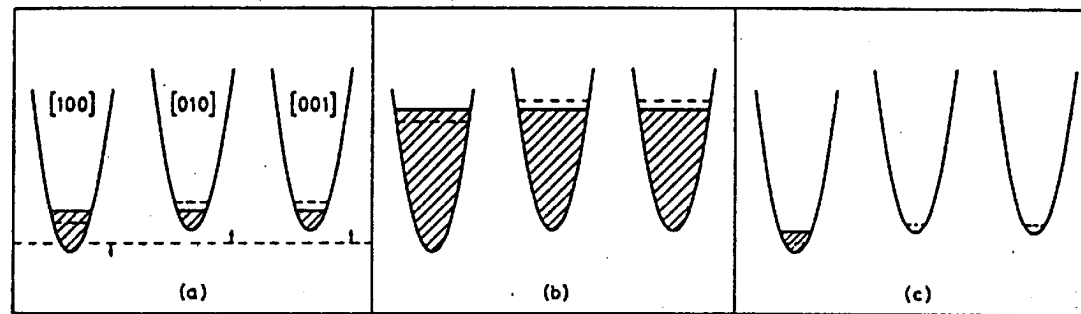
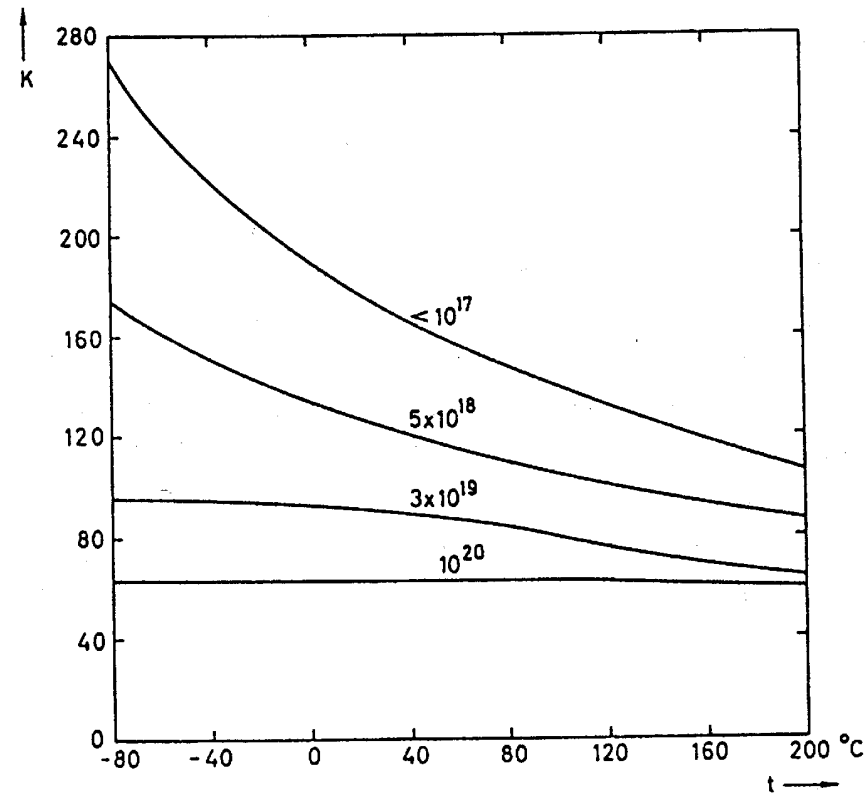


Fig. 3.5 (a) Upon compression in the [100] direction, the [100] energy minimum is lowered and the [010] and [001] minima are raised. Electrons flow from the [010] and [001] minima to the [100] minimum, (b) and (c) show the influence of the electron occupancy of the conduction band on the flow of electrons for high and low impurity concentration.

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† Piezoresistive respons to dopants and temperature

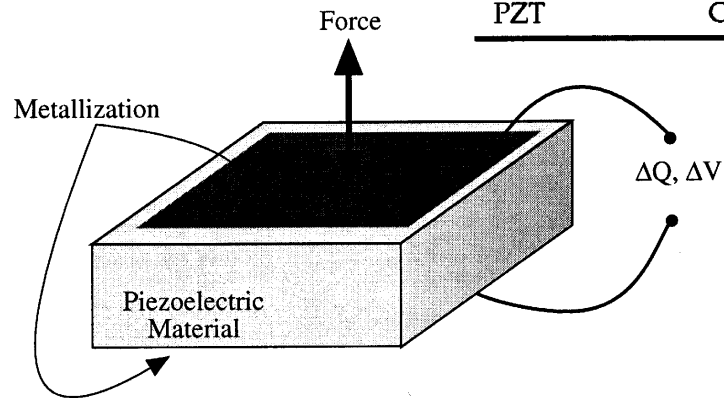


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† Piezoelectric sensing

Table 7.14 Piezoelectric coefficients of materials at 300 K.

Material	Type	Form	Coefficient, Ξ_{33} (pC/N)	Permittivity, ϵ_r
Quartz (X-cut)	Glass	Bulk	2.33	4.0
PVDF	Polymer	Film	1.59	-
P(VDF-TrFE)	Polymer	Film	18.0	6.2
ZnO	Ceramic	Bulk	11.7	9.0
ZnO	Ceramic	Film	12.4	10.3
BaTiO ₃	Ceramic	Bulk	190	4,100
PZT	Ceramic	Bulk	370	300- 3,000

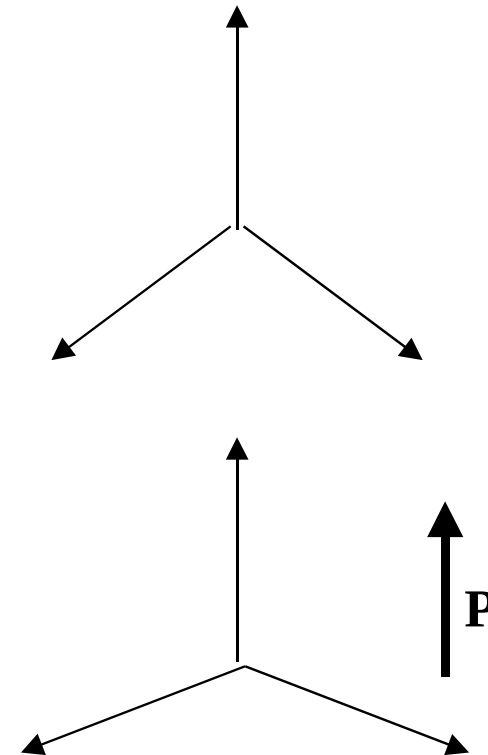


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† Piezoelectric mechanism

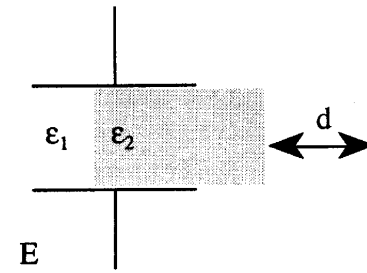
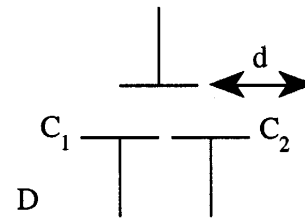
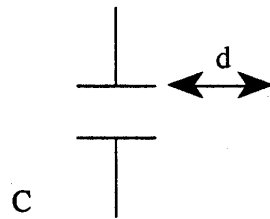
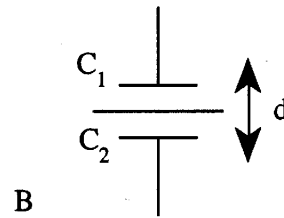
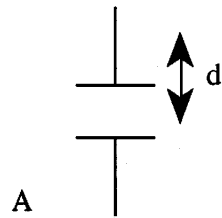
- Charge generation due to polarization to an applied force.
- With two conductors to the piezoelectric dielectric a capacitor is created, and we may measure a voltage difference.



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† Capacitive sensing



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† Micromechanical sensors:

- Strain gauges
- Accelerometers
- Gyroscopes
- Pressure sensors
- Microphones
- Tactile sensors
- Position sensors
- Flow sensors

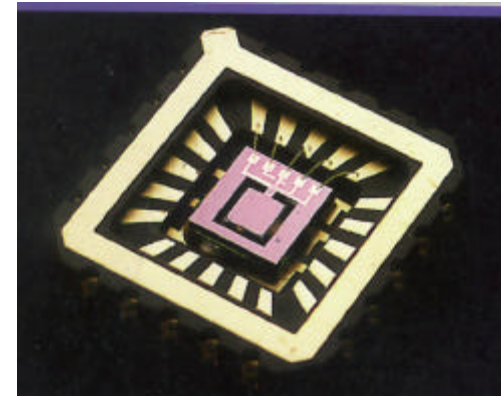
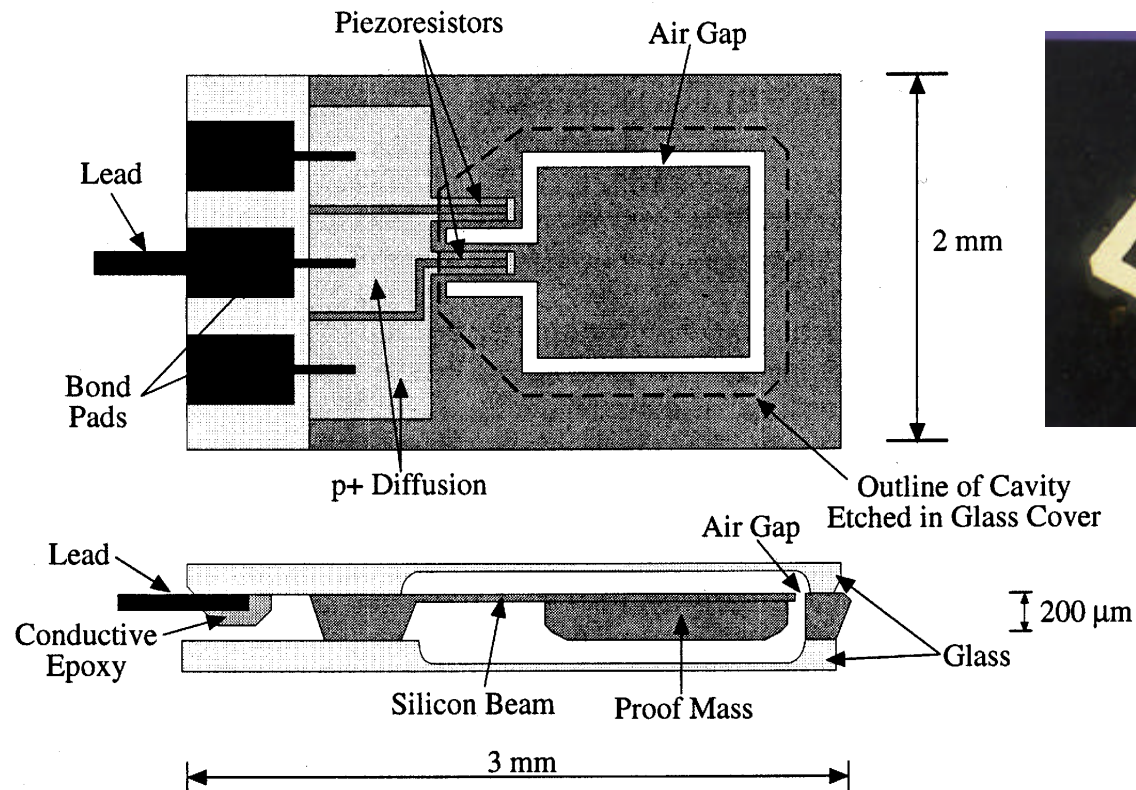
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† Accelerometer ranges and applications

Range	$\pm 1 \text{ g}$	antilock braking (ABS)/traction control system (TCS)
	$\pm 2 \text{ g}$	vertical body motion
	$\pm 40 \text{ g}$	wheel motion
	$\pm 50 \text{ g}$	air bag deployment
	$\pm 100^\circ/\text{s}$	steering feedback
Accuracy	$\pm 2 \%$	5% at temperature extremes
Cross-Axis Sensitivity	$< 1 \text{ to } 3 \%$	all applications
Shock Survivability	$> 500 \text{ g}$	1 m drop onto concrete
Frequency Response	0 to 5 Hz	vertical motion
	0.5 to 50 Hz	horizontal motion (up to 1 kHz for air bags)
Temperature Range	-40 to 85°C	most applications
	-40 to 125°C	under hood

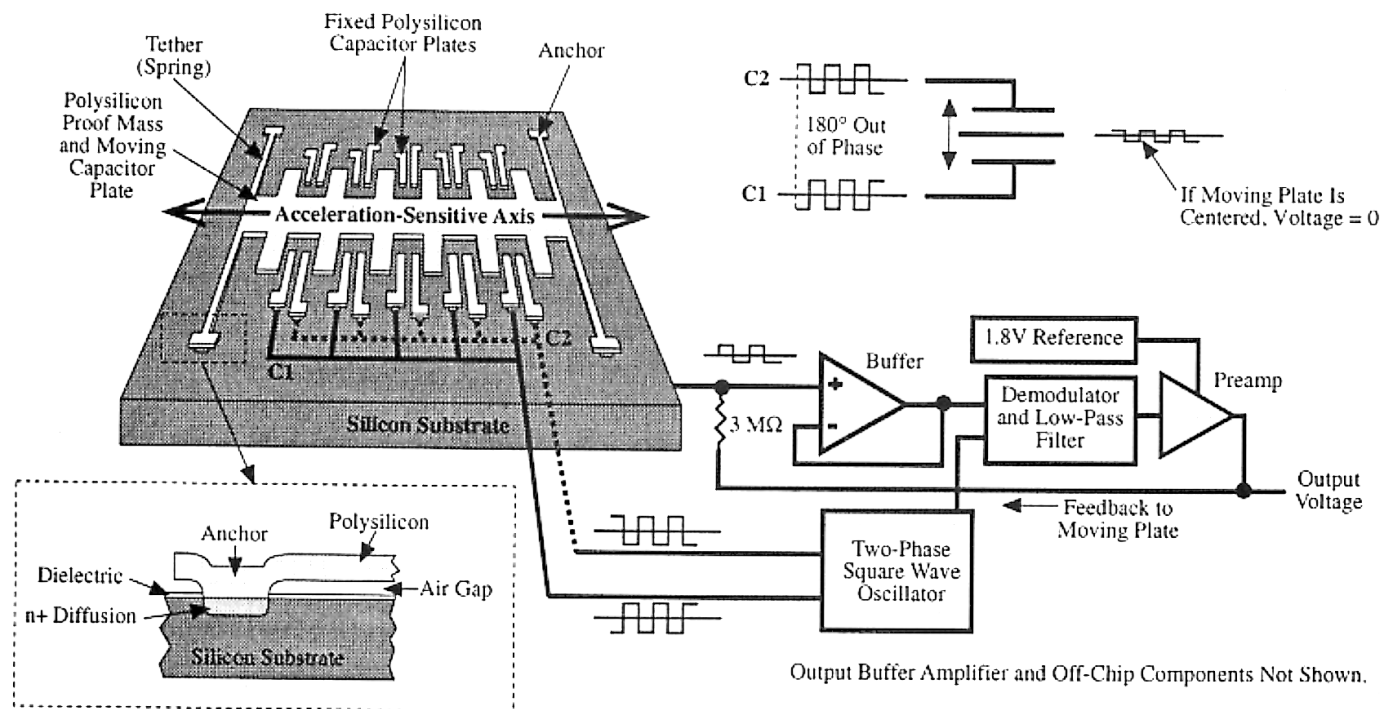
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† Bulk micromachined accelerometer



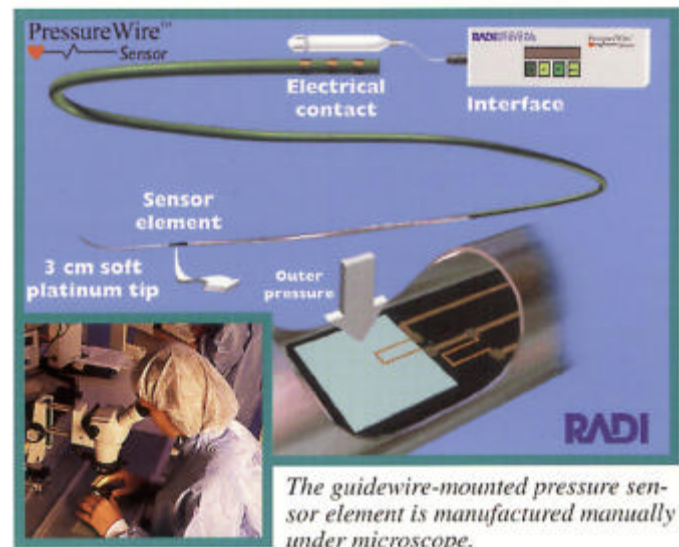
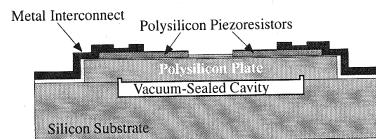
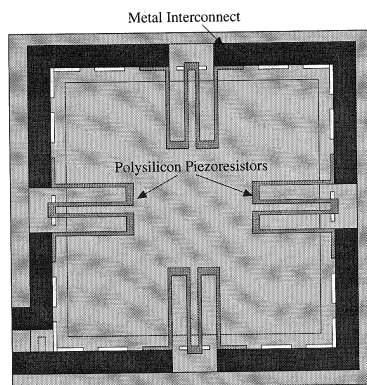
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† Surface micromachined accelerometer (AD):



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† Pressure sensor (Radi Medical Systems AB)



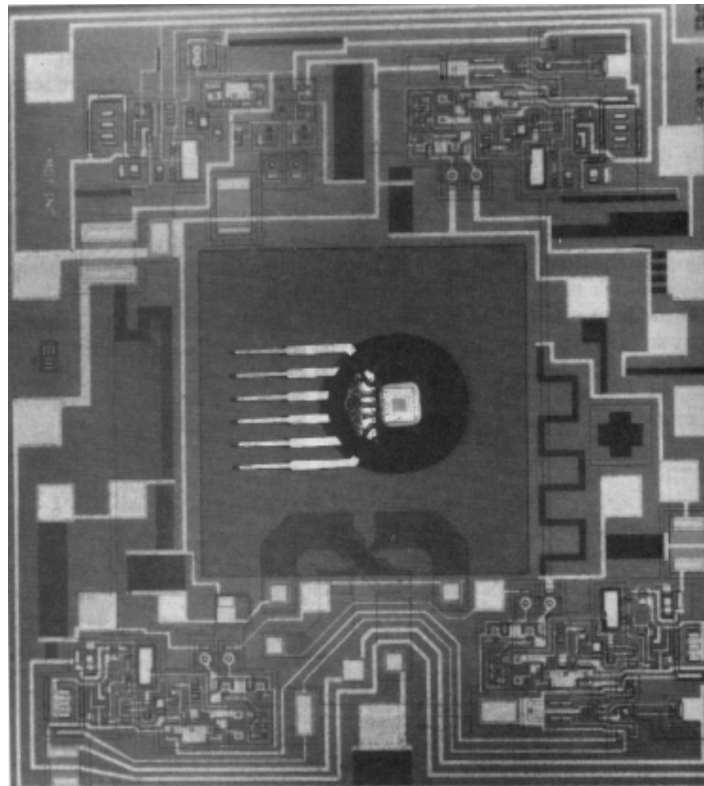
The guidewire-mounted pressure sensor element is manufactured manually under microscope.



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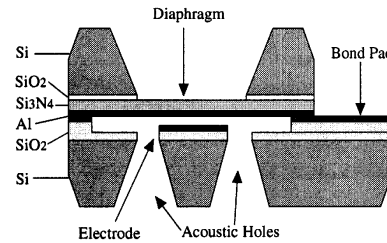


† Smart pressure sensor chip

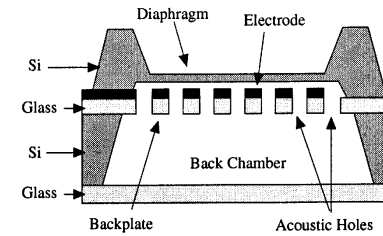


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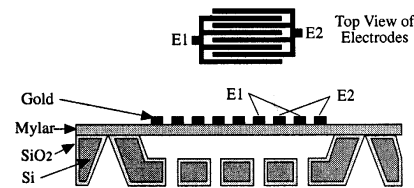
† Micromachined microphones



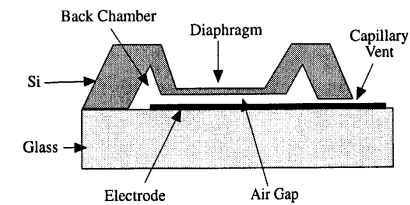
After Hohm (1986)



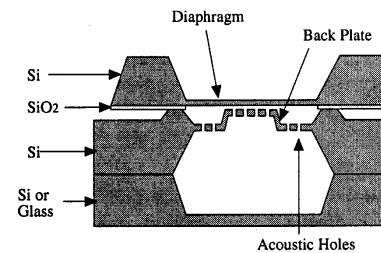
After Bergqvist and Rudolf (1990)



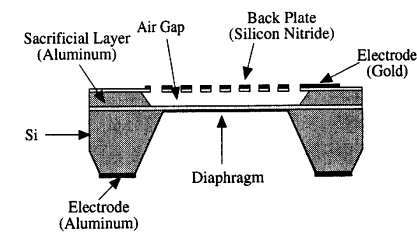
After van der Donk (1992)



After Bourouina, et al. (1992)



After Bergqvist, et al. (1991)

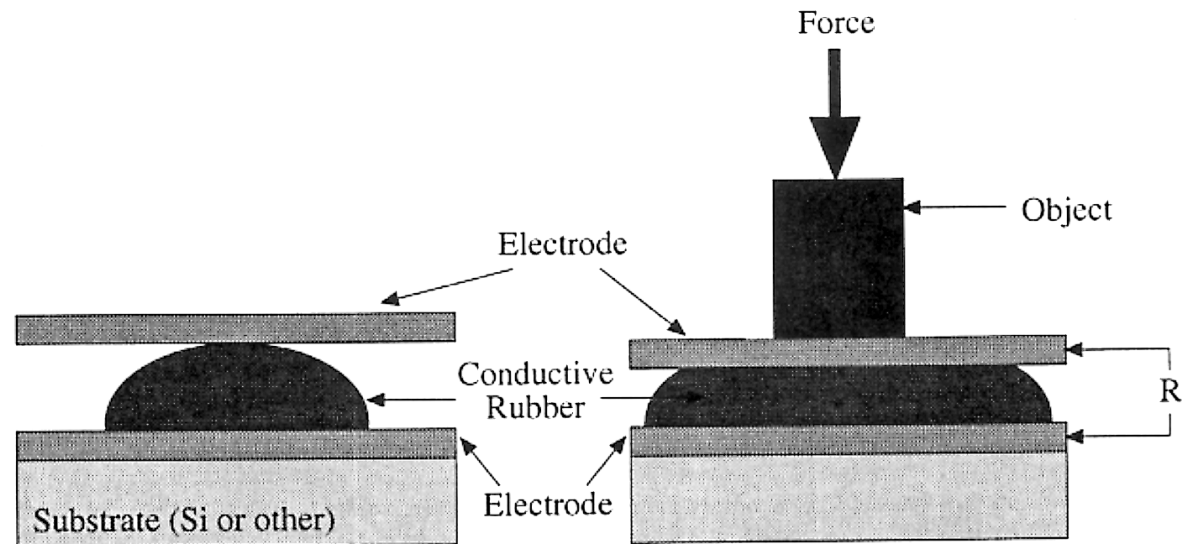


After Scheeper, et al. (1992)

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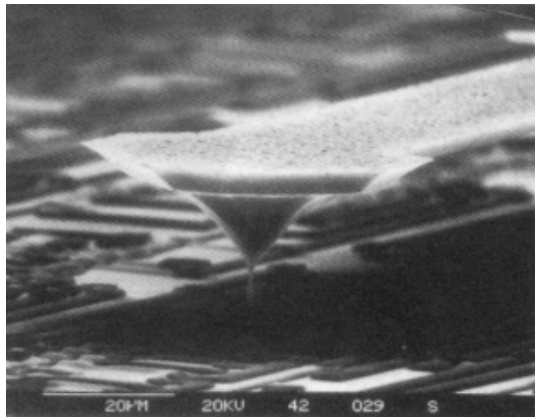
† Tactile sensor



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† Tunneling



$$I = I_0 e^{(-\beta\sqrt{\phi}z)}$$

where,

I_0 = scaling factor, dependent on materials, tip shape, etc.

β = conversion factor, typical value = $10.25 \text{ eV}^{-1/2}/\text{nm}$

ϕ = tunnel barrier height in electronvolts (eV), typical value = 0.5 eV

z = tip/surface separation in nanometers (nm), typical value = 1 nm

SENSORS and TRANSDUCERS



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† Micromechanics, more...

- Principle of detection: resonant
- Micromechanical resonant sensors: gyroscopes
- Micromechanic actuators

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† Resonators - applications

- Mechanical sensors, measuring strain
- Microbalances, measuring mass
- Chemical or biological sensors, measuring mass
- High-Q electrical filters

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† Simple dynamics:

$$m \frac{d^2x}{dt^2} + b \frac{dx}{dt} + kx = F_{\text{external}}$$

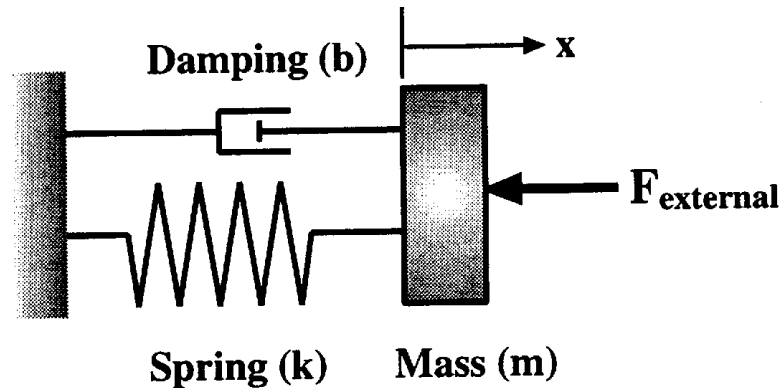
where,

m = mass, in kg

b = damping coefficient, in (N•s)/m

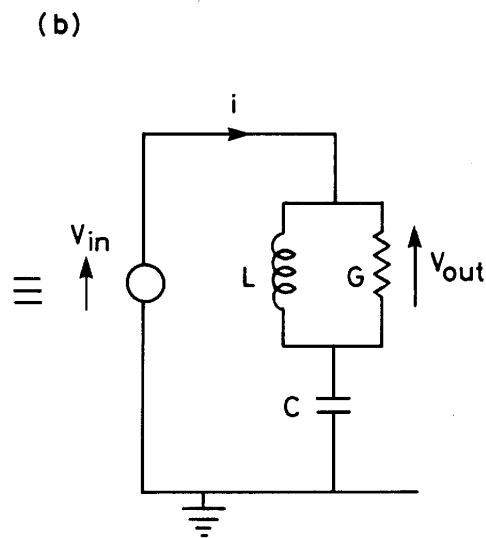
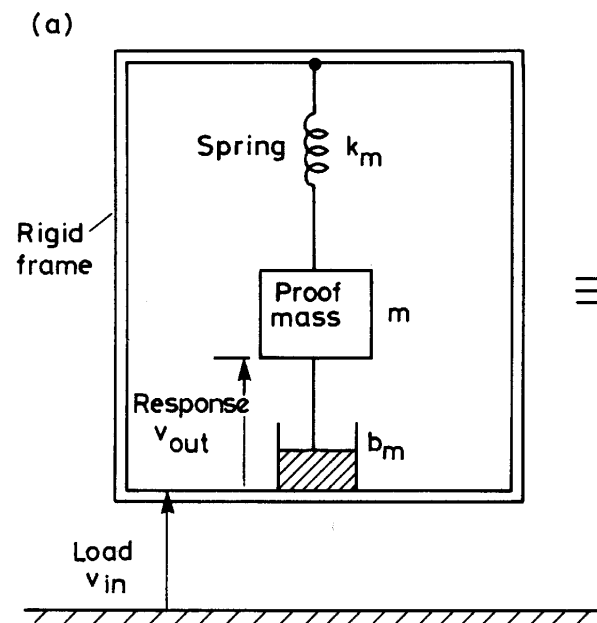
k = spring constant, in N/m

F_{external} = applied force, in N = (kg•m)/s²

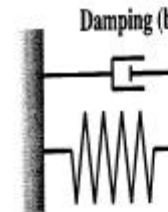


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† Dynamics in mechanics and electronics (1)



$$m \frac{d^2x}{dt^2} + b \frac{dx}{dt} + kx = F_{external}$$



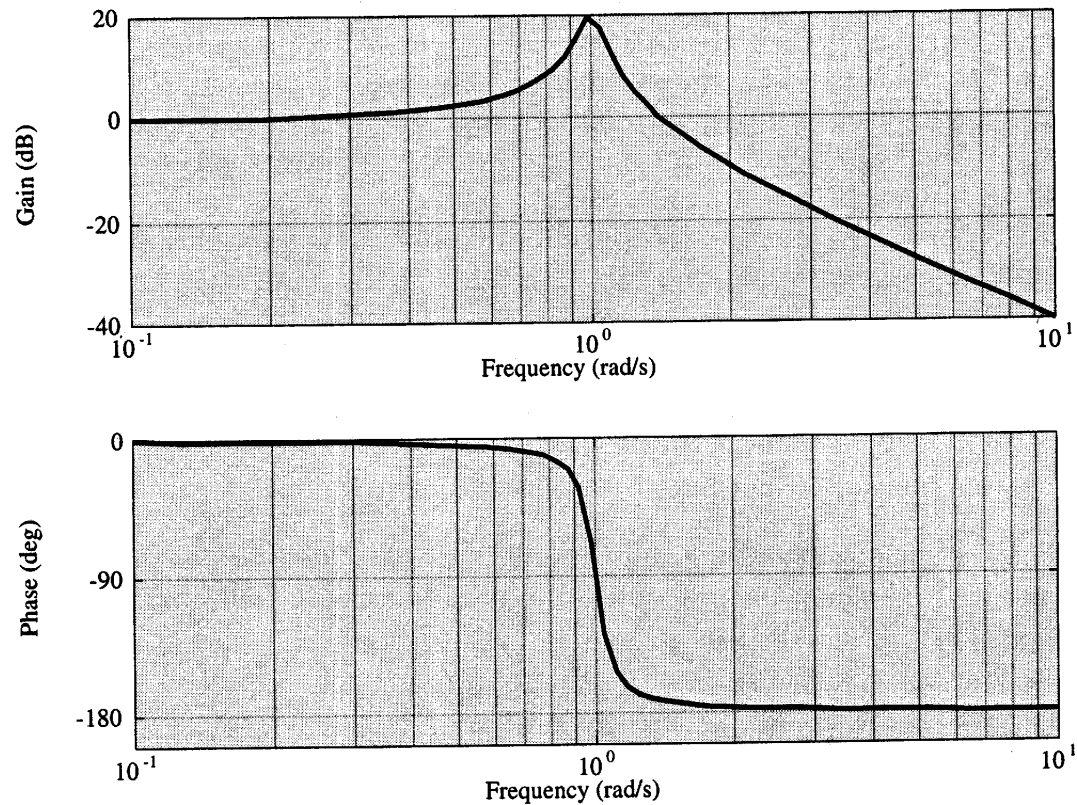
$$H(s) = \frac{\frac{1}{m}}{s^2 + \left(\frac{b}{m}\right)s + \frac{k}{m}}$$

$$H(S) = \frac{v_o}{v_i} = \frac{\frac{1}{LC}}{s^2 + \left(\frac{1}{RC}\right)s + \frac{1}{LC}} = \frac{\omega_o^2}{s^2 + \frac{\omega_o}{Q}s + \omega_o^2}$$

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† Dynamics in mechanics and electronics (2)



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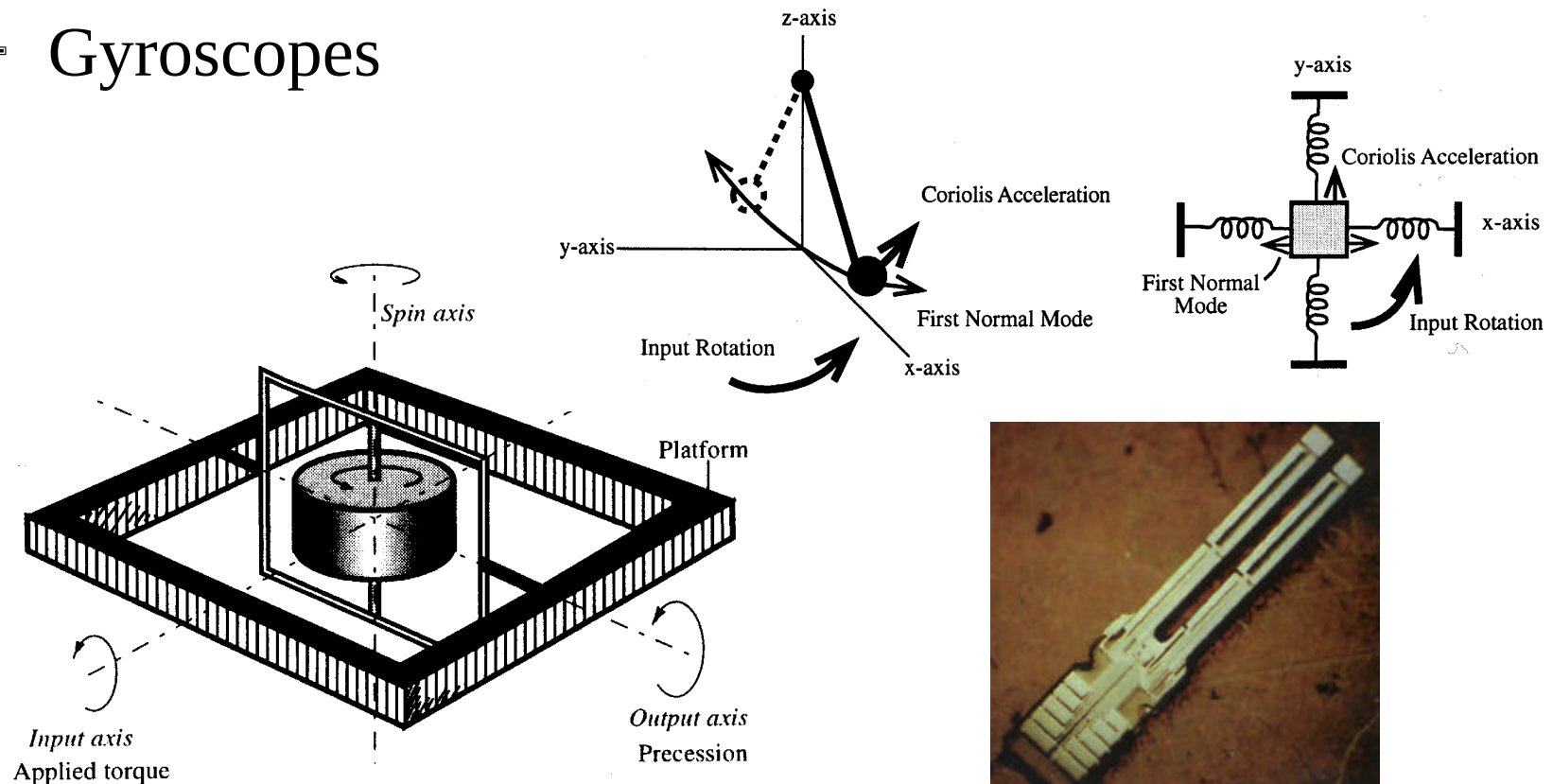
† Dynamics in mechanics and electronics (3)

$$Q = \frac{\text{energy stored per cycle}}{\text{energy lost per cycle}} = \omega_o RC \quad \text{where} \quad \omega_o = \frac{1}{\sqrt{LC}}$$

Parameter	Mechanical System	Electrical System
DC Gain	$\frac{1}{k}$	1
Natural Frequency, ω_o	$\sqrt{\frac{k}{m}}$	$\frac{1}{\sqrt{LC}}$
Quality Factor, Q	$\omega_o \frac{m}{b} = \sqrt{\frac{km}{b^2}}$	$\sqrt{\frac{R^2 C}{L}}$

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† Gyroscopes



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† Applications of micromechanical gyroscopes

Automotive safety reliable, inexpensive, lifetime, rough environment	- improved controls for airbags - anti-collision systems - active suspension - anti-skid	50g, 200°/s 100°/s 50°/s 100°/s	500mg, 10°/s 1°/s 2°/s 1°/s
Consumer inexpensive, small, lifetime, low-power	- free-space pointers (small computers) - remote control devices (TV-controls) - video camera (anti-jitter compensation) - navigation (complement to GPS) - toys and sports equipment	100°/s 100°/s 50°/s 50°/s varies	1°/s 2°/s 0.5°/s 0.5°/s varies
Industrial reliable, small, rough environment	- machine control - angular vibration measurements - attitude control of flying objects - automatic guided vehicles - stabilised platforms - robotics	10°/s varies 20°/s 50°/s 20°/s 10°/s	0.01°/s varies 0.02°/s 0.2°/s 0.2°/s 0.01°/s
Medical reliable, small, low-power	- monitoring of body-movement - vibration diagnostics - controls for paralysed patients - surgical instruments - wheel-chairs	10g, 100°/s 0.1g, 50°/s 2g, 100°/s 20°/s 2g, 50°/s	100mg, 1°/s 1mg, 0.5°/s 20mg, 2°/s 0.1°/s 20mg, 0.2°/s
Military reliable, small, rough environment	- new weapon systems - smart ammunition	- -	- -

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- † Gyroscope for automotive applications (TEMIC/Colibri)

